## IN THE CLAIMS

- 1. (Currently Amended) An acoustic transducer assembly comprising:
  - a substrate having a topside and a backside;
  - a microfabricated acoustic transducer formed on the topside of the substrate; and
  - a damping material disposed on the backside of the substrate, the damping material having an acoustic impedance substantially equal to that of the substrate and suppressing substrate acoustic modes.
- (Currently Amended) An apparatus according to claim 1 wherein:
  the damping material is lossy; and has an
  the acoustic impedance of the damping material that is similar to the acoustic impedance
  of the substrate that of silicon and is lossy.
- 3 (Original) An apparatus according to claim 1 further including electronic circuits formed in the substrate.
- (Currently Amended) An apparatus according to claim 3 wherein the electronics circuits are in between the sensor transducer and the damping material.
- 5. (Original) An apparatus according to claim 1 wherein the substrate is a wafer.
- (Original) An apparatus according to claim 1 wherein the damping material suppresses a longitudinal ringing mode.
- (Original) An apparatus according to claim 1 wherein the damping material suppresses a lamb wave ringing mode.
- 8. (Original) An apparatus according to claim 1 wherein the microfabricated acoustic transducer operates at frequencies above 20 kHz.

09/971,095

2

19. (Currently Amended) A method for suppressing acoustic modes, the method comprising:

providing a substrate having a topside and a backside;

forming a microfabricated acoustic transducer on the topside of the substrate; and placing a damping material on the backside of the substrate, the damping material having an acoustic impedance substantially equal to that of the substrate and suppressing substrate acoustic modes.

- 20. (Currently Amended) The method of claim 19 wherein:
  - the damping material is lossy; and has an
  - the acoustic impedance of the damping material that is similar to the acoustic impedance of the substrate that of silicon and is lossy.
- 21. (Original) The method of claim 20 further comprising forming electronic circuits in the substrate.
- 22. (Currently Amended) The method of claim 21 wherein the electronics circuits are in between the sensor transducer and the damping material.
- 23. (Original) The method of claim 19 wherein the substrate is a wafer.
- 24. (Original) The method of claim 19 wherein the damping material suppresses a longitudinal ringing mode.
- 25. (Original) The method of claim 19 wherein the damping material suppresses a lamb wave ringing mode.
- 26. (Original) The method of claim 19 further comprising operating the microfabricated acoustic transducer at frequencies above 20 kHz.

09/971,095

3